150V PNP SMALL SIGNAL TRANSISTOR IN SOT23

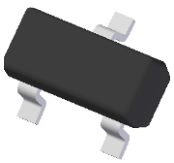
Features

- Epitaxial Planar Die Construction
- Complementary NPN Type - MMBT5551
- Ideal for Low Power Amplification and Switching
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP capable (Note 4)**

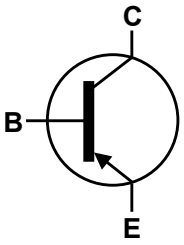
Mechanical Data

- Case: SOT23
- Case material: molded plastic, “Green” molding compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.008 grams (Approximate)

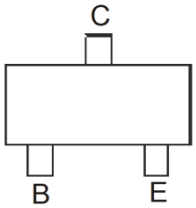
SOT23



Top View



Device Symbol



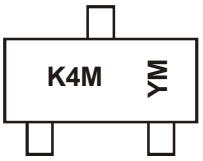
Top View
Pin-Out

Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBT5401-7-F	AEC-Q101	K4M	7	8	3,000
MMBT5401-13-F	AEC-Q101	K4M	13	8	10,000
MMBT5401Q-7-F	Automotive	K4M	7	8	3,000

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated’s definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen and Antimony free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



K4M = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: N = 2002)
M = Month (ex: 9 = September)

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015
Code	J	K	L	M	N	P	R	S	T	U	V	W	X	Y	Z	A	B	C

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-160	V
Collector-Emitter Voltage	V_{CEO}	-150	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-600	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

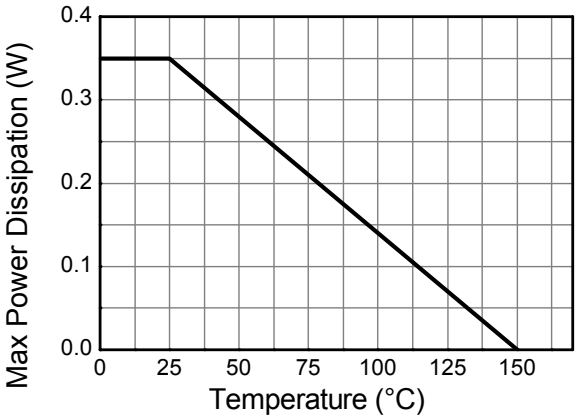
Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 6)	P_D	310	mW
	(Note 7)		350	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	403	°C/W
	(Note 7)		357	
Thermal Resistance, Junction to Leads	(Note 8)	$R_{\theta JL}$	350	°C/W
Operating and Storage Temperature Range		T_J,T_{STG}	-55 to +150	°C

ESD Ratings (Note 9)

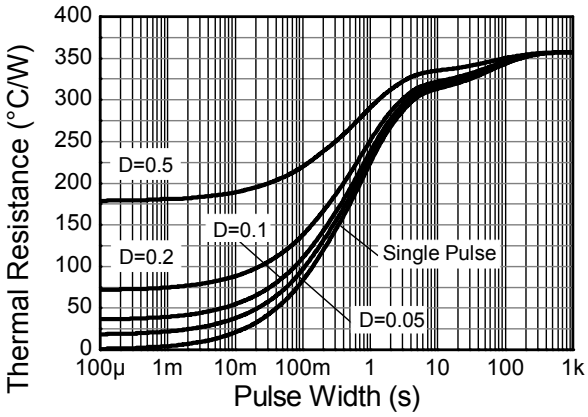
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

Notes:
6. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
7. Same as note (6), except the device is mounted on 15 mm x 15mm 1oz copper.
8. Thermal resistance from junction to solder-point (at the end of the leads).
9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

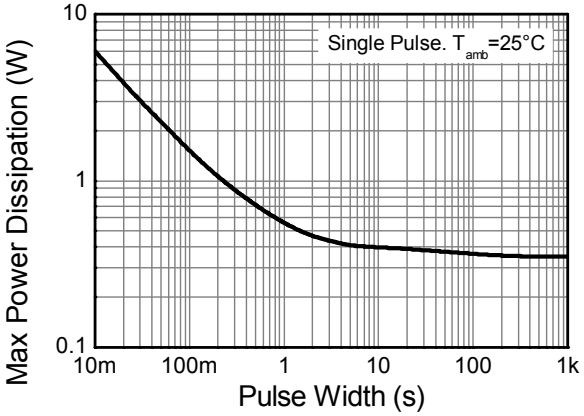
Thermal Characteristics and Derating Information



Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 10)					
Collector-Base Breakdown Voltage	BV_{CBO}	-160	—	V	I_C = -100μA, I_E = 0
Collector-Emitter Breakdown Voltage	BV_{CEO}	-150	—	V	I_C = -1.0mA, I_B = 0
Emitter-Base Breakdown Voltage	BV_{EBO}	-5.0	—	V	I_E = -10μA, I_C = 0
Collector Cutoff Current	I_{CBO}	—	-50 -50	nA μA	V_{CB} = -120V, I_E = 0 V_{CB} = -120V, I_E = 0, T_A = +100°C
Emitter Cutoff Current	I_{EBO}	—	-50	nA	V_{EB} = -4.0V, I_C = 0
ON CHARACTERISTICS (Note 10)					
DC Current Gain	h_{FE}	50 60 50	— 240 —	—	I_C = -1.0mA, V_{CE} = -5.0V I_C = -10mA, V_{CE} = -5.0V I_C = -50mA, V_{CE} = -5.0V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	-0.2 -0.5	V	I_C = -10mA, I_B = -1.0mA I_C = -50mA, I_B = -5.0mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	-1.0	V	I_C = -10mA, I_B = -1.0mA I_C = -50mA, I_B = -5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	6.0	pF	V_{CB} = -10V, f = 1.0MHz, I_E = 0
Small Signal Current Gain	h_{fe}	40	200	—	V_{CE} = -10V, I_C = -1.0mA, f = 1.0kHz
Current Gain-Bandwidth Product	f_T	100	300	MHz	V_{CE} = -10V, I_C = -10mA, f = 100MHz
Noise Figure	NF	—	8.0	dB	V_{CE} = -5.0V, I_C = -200μA, R_S = 10Ω, f = 1.0kHz

Notes: 10. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

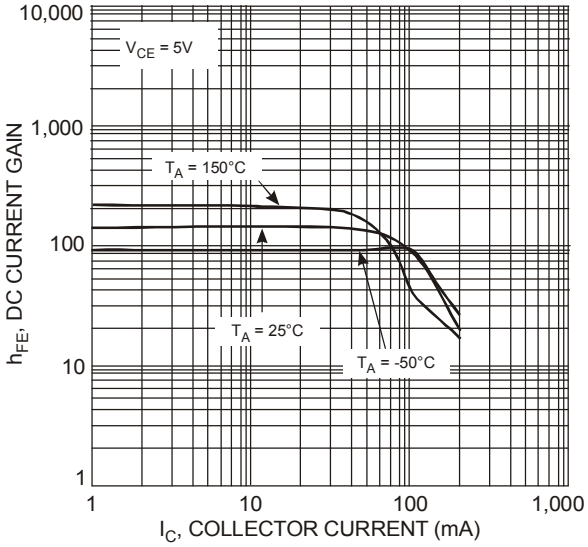


Fig. 2 Typical DC Current Gain vs. Collector Current

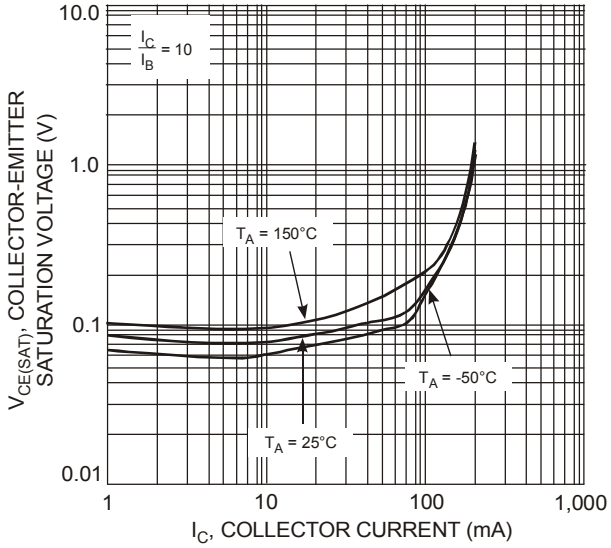


Fig. 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current

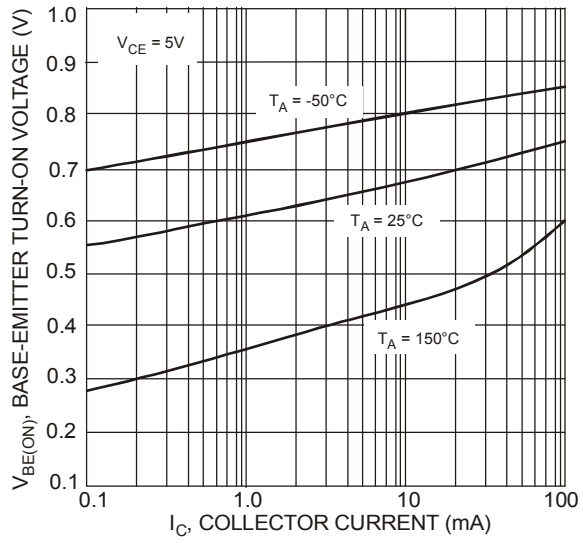


Fig. 4 Typical Base-Emitter Turn-On Voltage vs. Collector Current

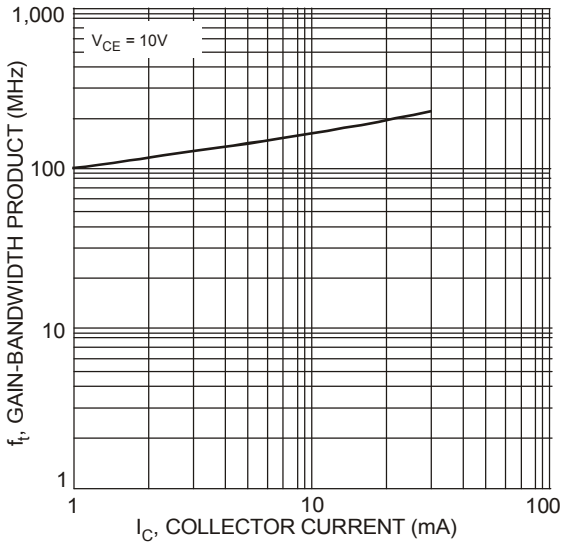
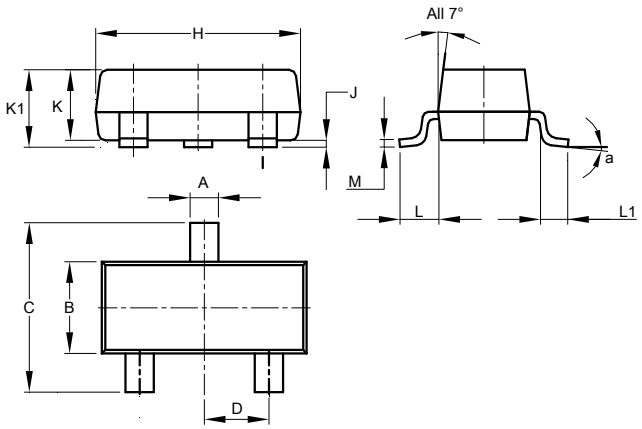


Fig. 5 Typical Gain-Bandwidth Product vs. Collector Current

Package Outline Dimensions

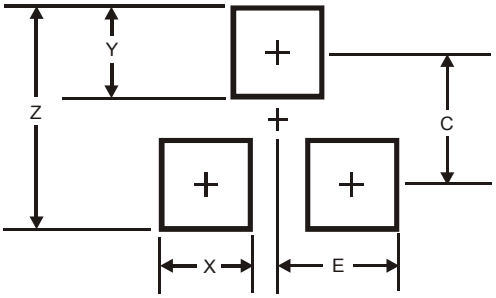
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	8°		
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.

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